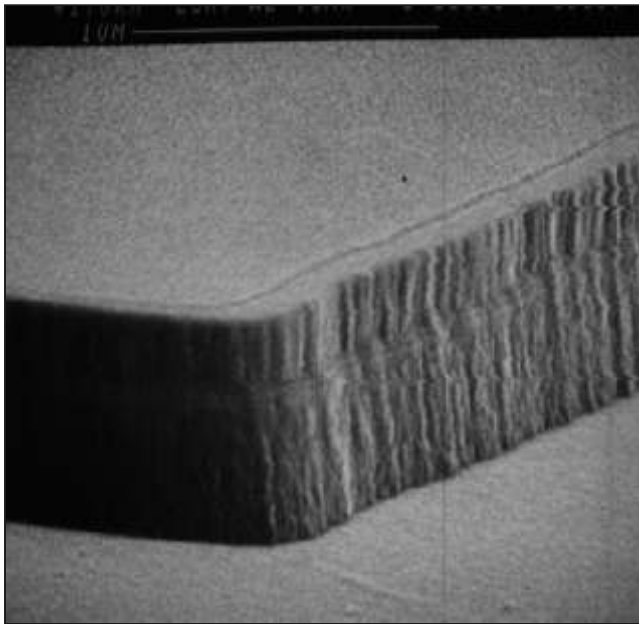
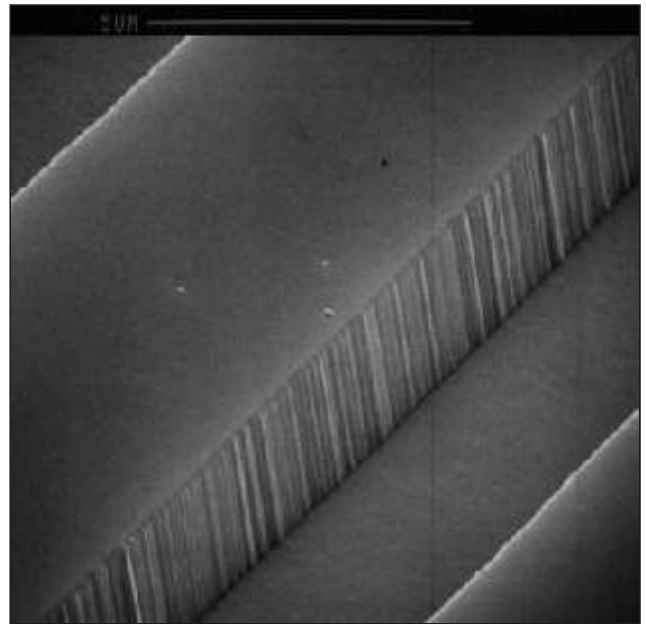


# Plasmalab Data

## *AllnP - Reactive Ion Etching*



1 µm AllnP etched with CH<sub>4</sub>

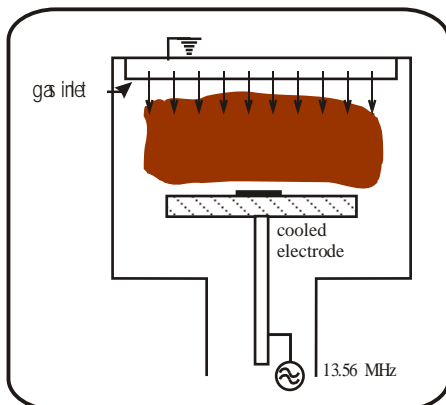


4 µm AllnP etched with SiCl<sub>4</sub>



*Plasmalab System 100  
Plasmalab System 133*

*Plasmalab 80 Plus*



### Technology:

Parallel Plate Configuration  
RIE-Mode (13.56 MHz)  
Shower Head Gas Inlet

### Results:

Rate :ca. 2 (CH<sub>4</sub>) - 25 (SiCl<sub>4</sub>) nm/ min  
Mask: Photoresist or SiO<sub>2</sub>  
60° - 85° walls (depending on mask)  
smoother walls by SiCl<sub>4</sub>